



# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

BC846/BC847/BC848

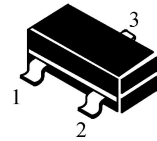
## SOT-23 Bipolar Transistor 双极型三极管

SOT-23

### ■ Features 特点

NPN General Purpose 通用

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



### ■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	BC846 A/B/C	BC847 A/B/C	BC848 A/B/C	Unit 单位
Collector-Base Voltage 集电极基极电压	$V_{CBO}$	80	50	30	V
Collector-Emitter Voltage 集电极发射极电压	$V_{CEO}$	65	45	30	V
Emitter-Base Voltage 发射极基极电压	$V_{EBO}$	6	6	5	V
Collector Current 集电极电流	$I_C$	100			mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	200			mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	625			$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-55to+150 $^\circ\text{C}$			

### ■ Device Marking 产品打标

$H_{FE}$		110-220(A)	200-450(B)	420-800(C)
Mark	BC846	1A	1B	1C
	BC847	1E	1F	1G
	BC848	1J	1K	1L



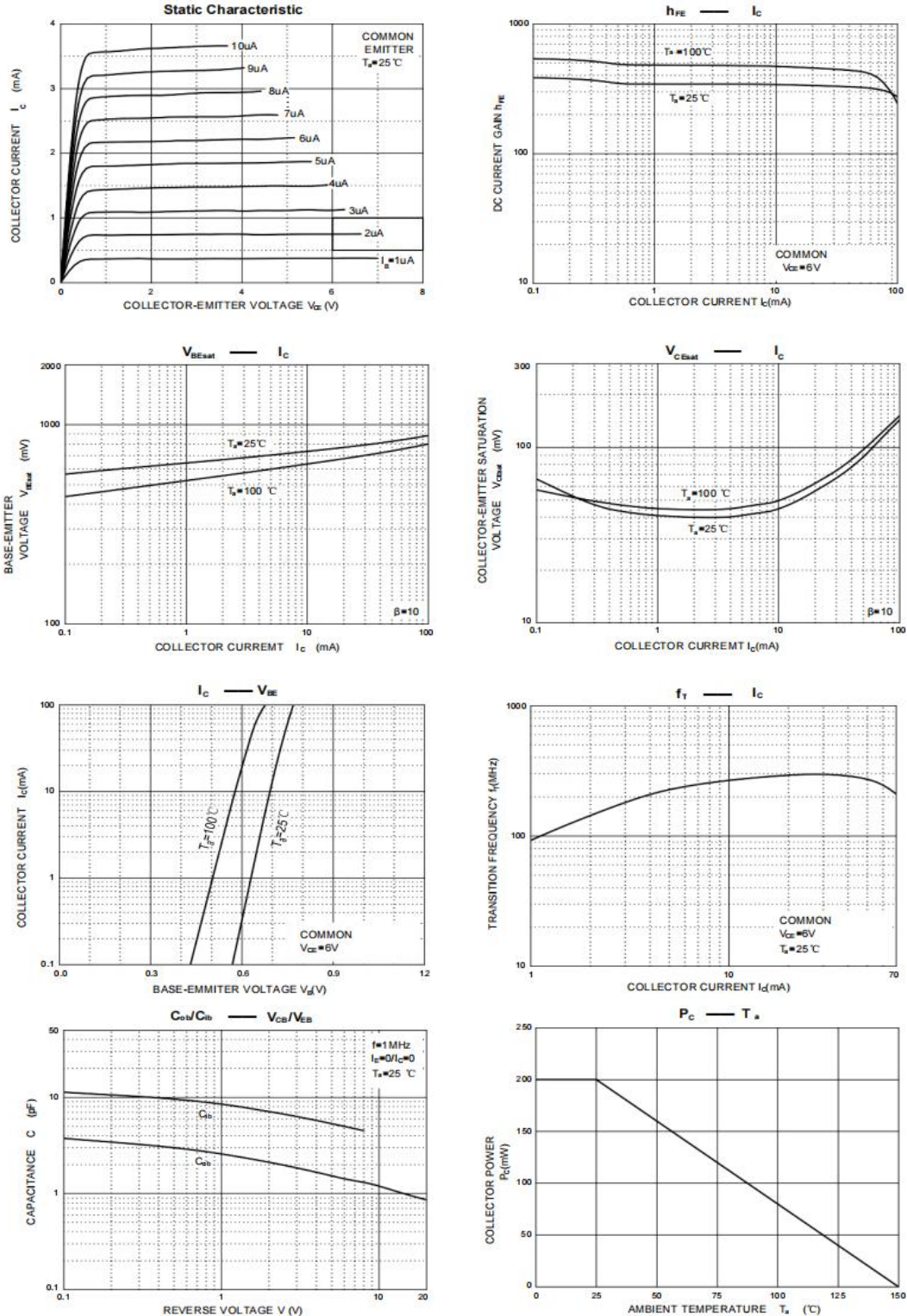
## ■ Electrical Characteristics 电特性

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

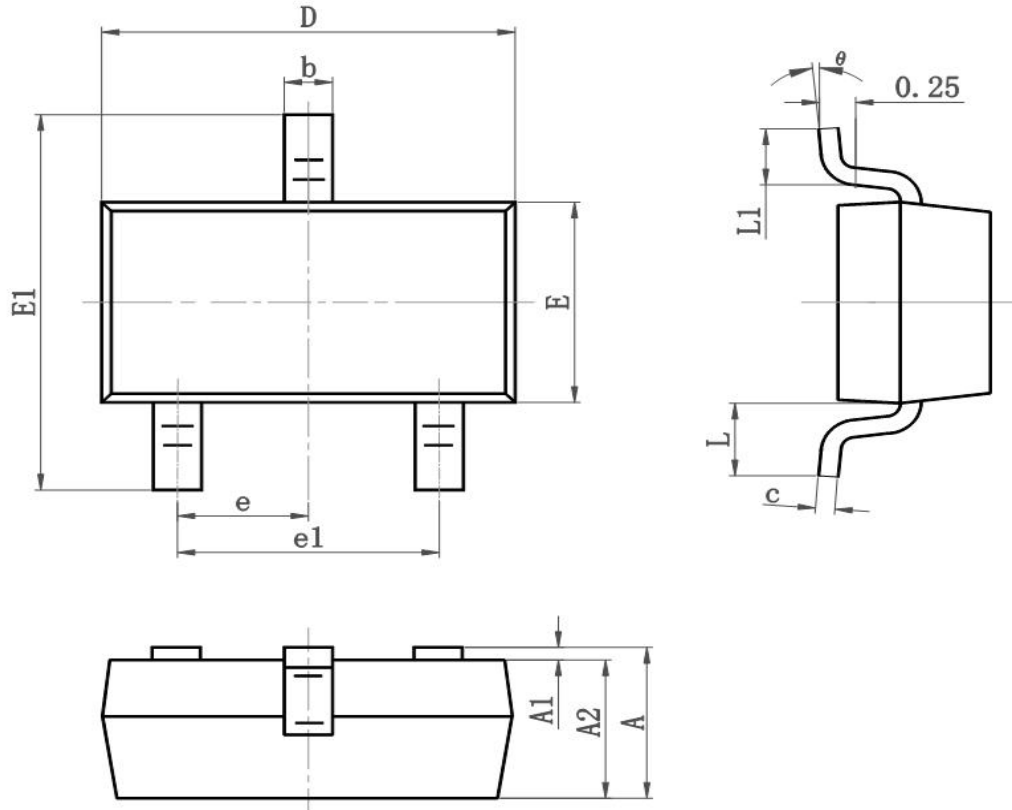
Characteristic 特性参数		Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压 ( $I_C=10\mu\text{A}$ , $I_E=0$ )	BC846A/B/C BC847A/B/C BC848A/B/C	$BV_{CBO}$	80 50 30	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压 ( $I_C=10\text{mA}$ , $I_B=0$ )	BC846A/B/C BC847A/B/C BC848A/B/C	$BV_{CEO}$	65 45 30	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压 ( $I_E=10\mu\text{A}$ , $I_C=0$ )		$BV_{EBO}$	5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流	BC846A/B/C( $V_{CB}=70\text{V}, I_E=0$ ) BC847A/B/C( $V_{CB}=50\text{V}, I_E=0$ ) BC848A/B/C( $V_{CB}=30\text{V}, I_E=0$ )	$I_{CBO}$	—	—	100	nA
Emitter-Base Leakage Current 发射极基极漏电流 ( $V_{EB}=5\text{V}$ , $I_C=0$ )		$I_{EBO}$	—	—	100	nA
DC Current Gain 直流电流增益 ( $V_{CE}=5\text{V}, I_C=2\text{mA}$ )	BC846A/BC847A/BC848A BC846B/BC847B/BC848B BC846C/BC847C/BC848C	$H_{FE}$	110 200 420	180 290 520	220 450 800	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降 ( $I_C=100\text{mA}$ , $I_B=5\text{mA}$ )		$V_{CE(sat)}$	—	—	0.5	V
Base-Emitter Saturation Voltage 基极发射极饱和压降 ( $I_C=100\text{mA}$ , $I_B=5\text{mA}$ )		$V_{BE(sat)}$	—	—	1.1	V
Transition Frequency 特征频率 ( $V_{CE}=5\text{V}$ , $I_C=10\text{mA}$ )		$f_T$	100	—	—	MHz
Output Capacitance 输出电容 ( $V_{CB}=10\text{V}$ , $I_E=0$ , $f=1\text{MHz}$ )		$C_{ob}$	—	4.5	—	pF



## Typical Characteristic Curve 典型特性曲线



## ■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
$\theta$	$0^\circ$	$8^\circ$	$0^\circ$	$8^\circ$